Microwave GaAs Power FET Amplifiers with Lumped-Element Impedance Matching Networks

H.Q. Tserng and H.M. Macksey. "Microwave GaAs Power FET Amplifiers with Lumped-Element Impedance Matching Networks." 1978 MTT-S International Microwave Symposium Digest 78.1 (1978 [MWSYM]): 282-284.

Lumped-element impedance matching has been used successfully for the design of GaAs power FET amplifiers at C- and X bands. It is shown that output powers up to 8W with 1 dB bandwidth of from 1 to 5 GHz can be obtained.

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